

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
-20V	75mΩ @ V _{GS} = -4.5V	-3.8A
	137mΩ @ V _{GS} = -2.5V	-2.8A

Description

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, which makes it ideal for high-efficiency power management applications.

Applications

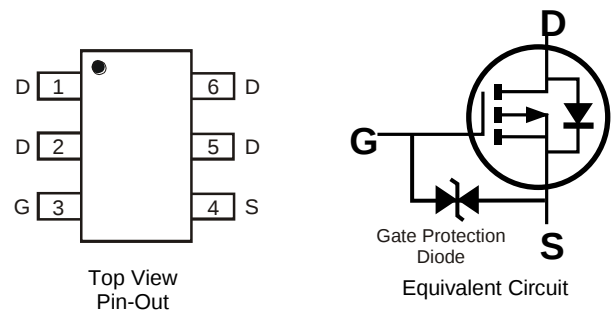
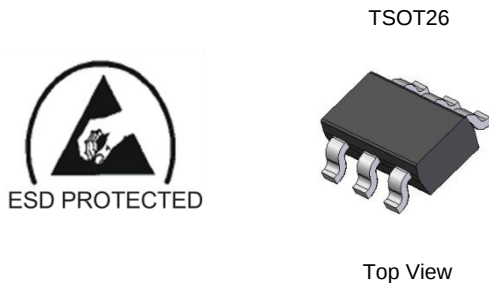
- General Purpose Interfacing Switch
- Power Management Functions

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: TSOT26
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe.
Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.015 grams (Approximate)

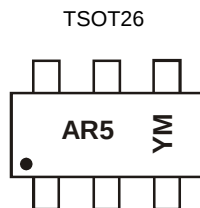


Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2075UVT-7	TSOT26	3000/Tape & Reel
DMP2075UVT-13	TSOT26	10,000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



AR5 = Product Type Marking Code
YM = Date Code Marking
Y or Y̅ = Year (ex: F = 2018)
M = Month (ex: 9 = September)

Date Code Key

Date Code Key

Year	2018	2019	2020	2021	2022	2023	2024	2025	2026
Code	F	G	H	I	J	K	L	M	N

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 6) V _{GS} = -4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	-3.8 -3.0	A
Maximum Continuous Body Diode Forward Current (Note 6)			I _S	-2.1	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	-25	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Total Power Dissipation (Note 5)			P _D	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State		R _{θJA}	105	°C/W
Total Power Dissipation (Note 6)			P _D	1.6	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State		R _{θJA}	77	°C/W
Operating and Storage Temperature Range			T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1	μA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±8.0V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.3	—	-1.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	—	75	mΩ	V _{GS} = -4.5V, I _D = -4.0A
		—	—	137		V _{GS} = -2.5V, I _D = -3.5A
Diode Forward Voltage	V _{SD}	—	—	-1.2	V	V _{GS} = 0V, I _S = -1.0A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	642	—	pF	V _{DS} = -10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	98	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	87	—	pF	
Gate Resistance	R _g	—	26.5	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q _g	—	8.8	—	nC	V _{GS} = -4.5V, V _{DS} = -10V I _D = -4A
Gate-Source Charge	Q _{gs}	—	0.9	—	nC	
Gate-Drain Charge	Q _{gd}	—	2.9	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	5.5	—	ns	V _{DS} = -10V, V _{GS} = -4.5V, R _D = 2.5Ω, R _G = 3.0Ω, I _D = -1A
Turn-On Rise Time	t _r	—	22.6	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	34.1	—	ns	
Turn-Off Fall Time	t _f	—	34.3	—	ns	
Reverse Recovery Time	t _{RR}	—	13	—	ns	I _F = -1.0A, di/dt = 100A/μs
Reverse Recovery Charge	Q _{RR}	—	3.3	—	nC	I _F = -1.0A, di/dt = 100A/μs

- Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 7. Short duration pulse test used to minimize self-heating effect.
 8. Guaranteed by design. Not subject to product testing.

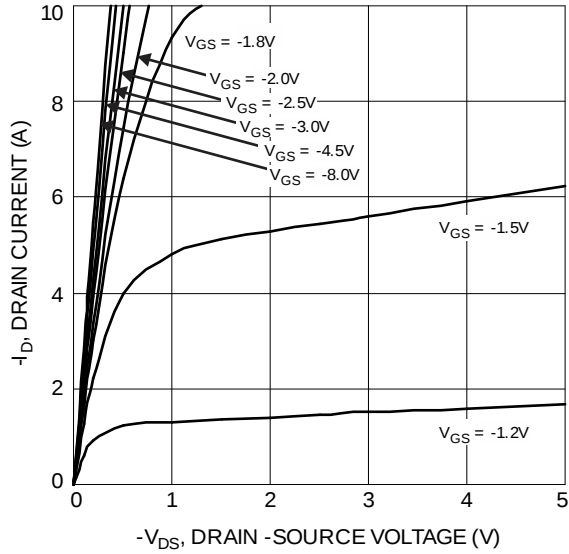


Figure 1 Typical Output Characteristics

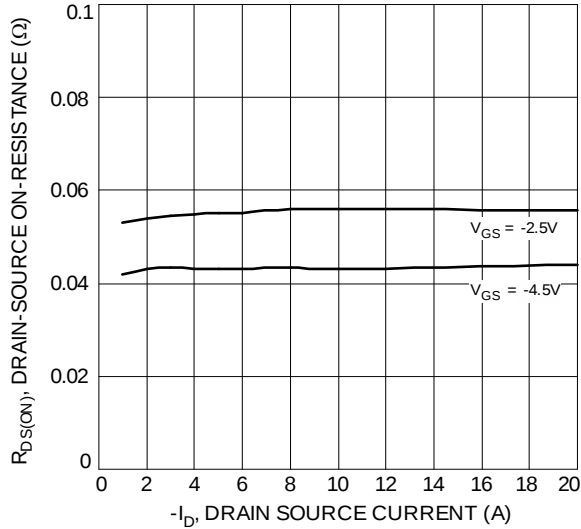


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

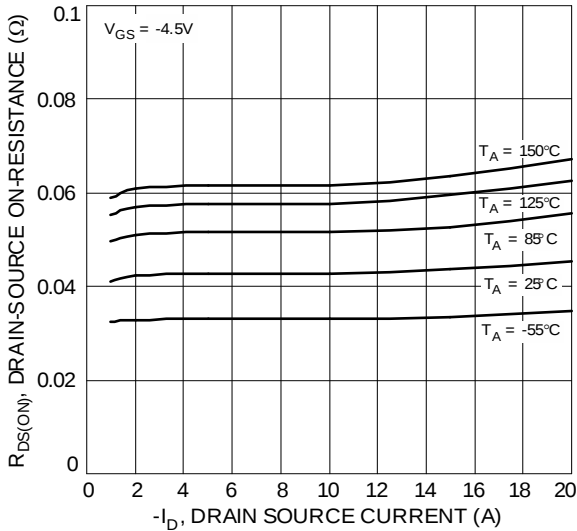


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

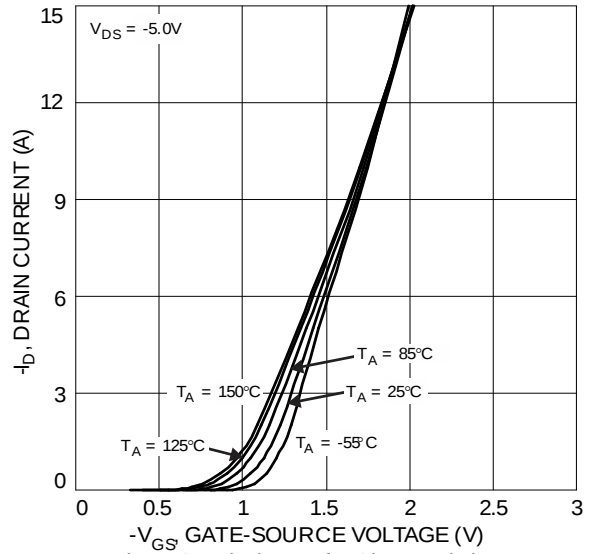


Figure 2 Typical Transfer Characteristics

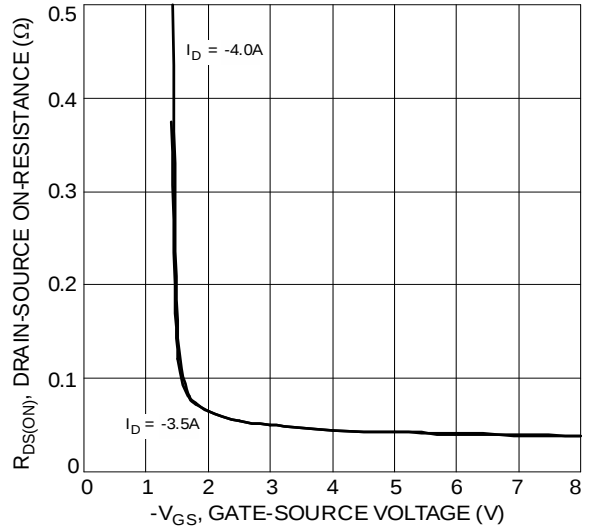


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

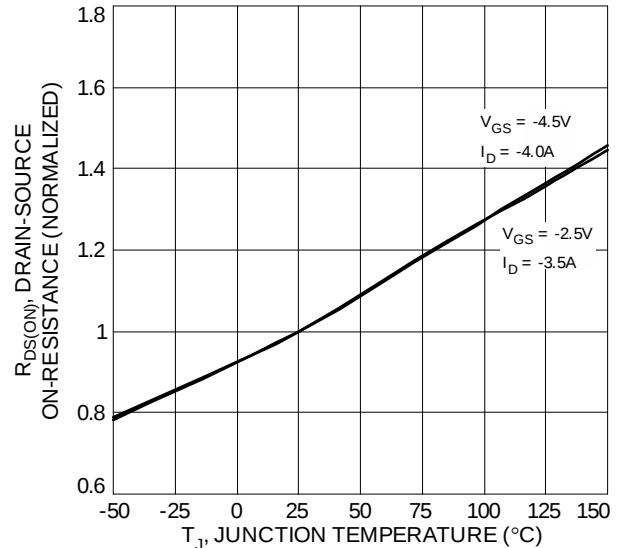
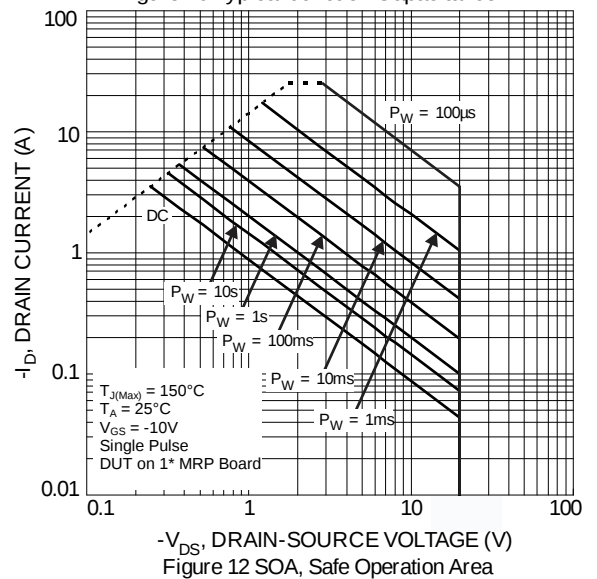
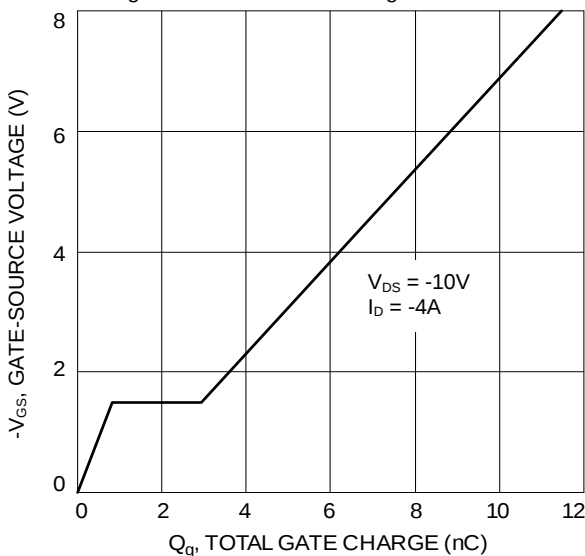
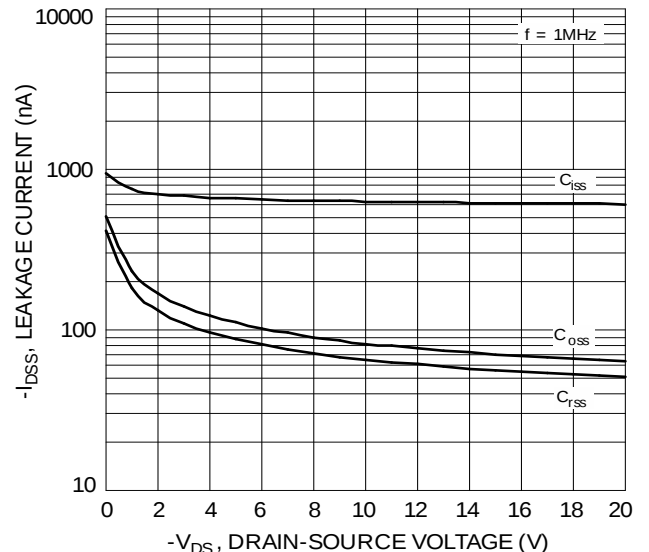
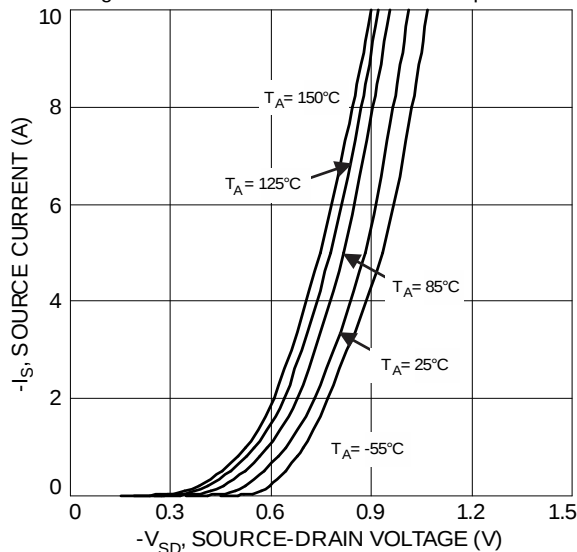
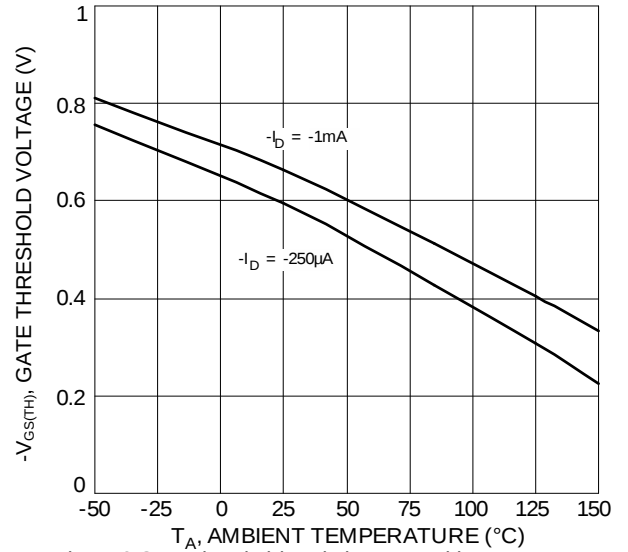
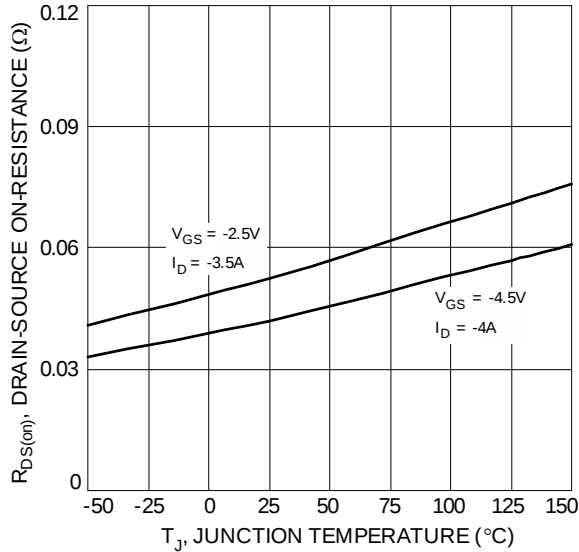


Figure 6 On-Resistance Variation with Temperature



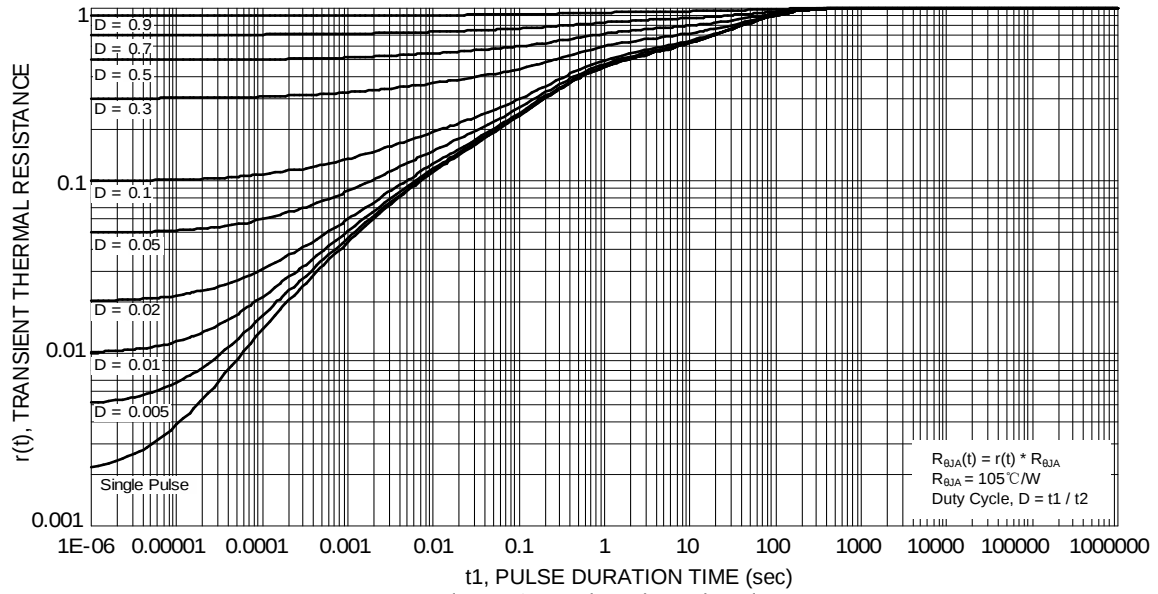
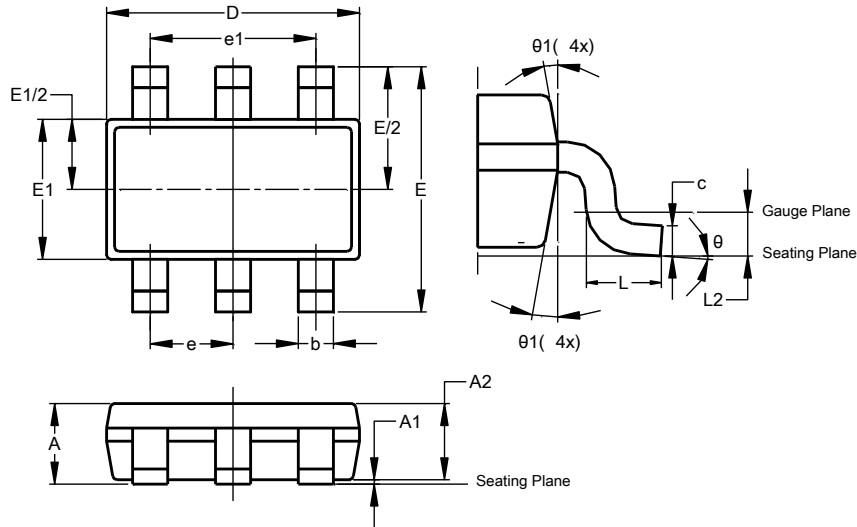


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TSOT26

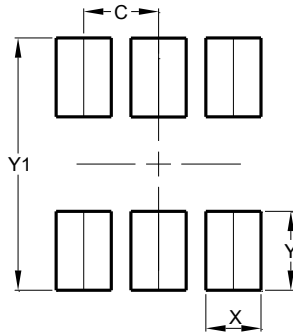


TSOT26			
Dim	Min	Max	Typ
A	—	1.00	—
A1	0.010	0.100	—
A2	0.840	0.900	—
D	2.800	3.000	2.900
E	2.800 BSC		
E1	1.500	1.700	1.600
b	0.300	0.450	—
c	0.120	0.200	—
e	0.950 BSC		
e1	1.900 BSC		
L	0.30	0.50	—
L2	0.250 BSC		
θ	0°	8°	4°
θ1	4°	12°	—
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TSOT26



Dimensions	Value (in mm)
C	0.950
X	0.700
Y	1.000
Y1	3.199

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